

TECHNICAL DATA DATA SHEET 686, REV. -

# HERMETIC POWER MOSFET N-CHANNEL

(PRELIMINARY)

DESCRIPTION: 30 VOLT, 20 AMP, 0.02 OHM MOSFET IN A HERMETIC TO-257 PACKAGE.

## **MAXIMUM RATINGS**

ALL RATINGS ARE AT  $T_{A} = 25^{\circ}\text{C}$  UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	$V_{GS}$	-	-	±15	Volts
CONTINUOUS DRAIN CURRENT V <sub>GS</sub> =10V, T <sub>C</sub> = 25°C	I <sub>D</sub>	-	-	20	Amps
$V_{GS}=10V, T_{C}=100^{\circ}C$				20	
PULSED DRAIN CURRENT @ T <sub>C</sub> = 25°C	I <sub>DM</sub>	-	-	100	Amps(pk)
OPERATING AND STORAGE TEMPERATURE	$T_{OP}/T_{STG}$	-55	-	+150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{ heta JC}$	-	-		°C/W
TOTAL DEVICE DISSIPATION @ T <sub>C</sub> = 25°C	$P_{D}$	-	-		Watts

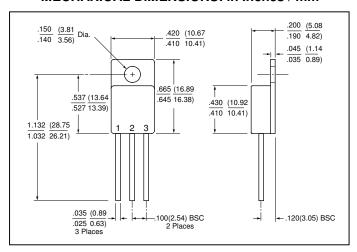
# **ELECTRICAL CHARACTERISTICS**

DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV <sub>DSS</sub>	30	-	-	Volts
$V_{GS} = 0V, I_D = 250\mu A$					
DRAIN TO SOURCE ON STATE RESISTANCE					
$I_D = 10A, V_{GS} = 5.0V@T_J = 25^{\circ}C$	R <sub>DS(ON)</sub>	-	6.0	20	mΩ
FORWARD TRANSCONDUCTANCE	9 <sub>fs</sub>	15	55	-	S(1/Ω)
$V_{DS} = 3.0 \text{Vdc}, I_{DS} = 37.5 \text{A}$					
ZERO GATE VOLTAGE DRAIN CURRENT		-	.05		μΑ
$V_{DS} = 30 \text{Vdc}, V_{GS} = 0 \text{Vdc}$	I <sub>DSS</sub>			10	
$V_{DS} = 30 \text{Vdc}$				100	
$V_{GS} = 0 Vdc, T_J = 125^{\circ}C$					
GATE TO BODY LEAKAGE CURRENT $V_{GS} = \pm 20 \text{Vdc}$ ,	$I_{GSS}$	-	-	+100	nA
$V_{DS} = 0Vdc$				-100	
TOTAL GATE CHARGE $(V_{GS} = 5.0 \text{ Vdc},$	$Q_g$		61	122	nC
GATE TO SOURCE CHARGE $V_{DS} = 24Vdc$ ,	$Q_gs$		14	28	
GATE TO DRAIN CHARGE $I_D = 75$ Adc)	$Q_gd$		33	66	
TURN ON DELAY TIME $(V_{DS} = 15V,$	$t_{d(ON)}$	-	24	48	nsec
RISE TIME $I_D = 75 Adc$ ,	t <sub>r</sub>		493	986	
TURN OFF DELAY TIME $V_{GS} = 5.0 \text{ Vdc}$ ,	t <sub>d(ON)</sub>		60	120	
FALL TIME $R_G = 4.7\Omega$ )	t <sub>f</sub>		149	300	
FORWARD VOLTAGE, $(I_S = 4.7Adc, V_{GS} = 0V)$	$V_{SD}$	-	0.97	1.1	Volts
$(I_S = 75 Adc, V_{GS} = 0 Vdc, T_J = 125 °C)$			0.87		
REVERSE RECOVERY TIME $(I_S = 75Adc, V_{GS} = 0Vdc)$	t <sub>rr</sub>	-	58	-	nsec
REVERSE RECOVERY CHARGE di/dt = 100A/μsec)	$Q_{rr}$		.088		μС
INPUT CAPACITANCE $(V_{DS} = 25 \text{ Vdc},$	$C_{iss}$	-	4025	5635	pF
OUTPUT CAPACITANCE $V_{GS} = 0 \text{ Vdc},$	$C_{oss}$		1353	1894	
REVERSE TRANSFER CAPACITANCE f = 1 MHz)	$C_{rss}$		307	430	

\*Note: Current limited by pin diameter.

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### **MECHANICAL DIMENSIONS:** in Inches / mm



TO-257

# **PINOUT TABLE**

DEVICE TYPE	PIN 1	PIN 2	PIN 3
MOSFET IN A TO-257 PACKAGE	DRAIN	SOURCE	GATE



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